



GAU 1746

[10191/955]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Joerg SCHAEFER, et al
SERIAL NO. : 09/238,262
FILED : January 27, 1999
TITLE : METHOD OF PRODUCING STRUCTURED
WAFERS
ART UNIT : 1746
EXAMINER : Anita K. Alanko

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Signature

Kenn E. Collins
KENYON & KENYON

Assistant Commissioner for Patents
Washington, D.C. 20231

AMENDMENT TRANSMITTAL

SIR:

Please find transmitted herewith for filing in the above-identified
patent application an Amendment.

No fee is believed to be required. However, if any fee is
required, please charge to Deposit Account No. **11-0600**. Similarly, please
credit any overpayment into Deposit Account No. **11-0600**. A duplicate copy
of this transmittal letter is enclosed for that purpose.

Respectfully submitted,

KENYON & KENYON

A212 M. Ahsan
Reg. No. 32,100By: for R. L. Mayer
Richard L. Mayer
Reg. No. 22,490Dated: Nov. 16, 2000

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Kelly E. Collins
KENYON & KENYON

Assistant Commissioner for Patents
Washington, D.C. 20231

AMENDMENT

Sir:

In response to the Office Action dated August 16, 2000, please reconsider the above identified application based on the following:

IN THE CLAIMS:

Please amend the claims as follows:

4. (Amended) The method according to claim 3, further comprising the steps of:
applying a [thin] further passivation layer in the subareas, after the removal of the nitride layer in the subareas and before the wafer is etched; and
completely removing the nitride layer.

5. (Amended) The method according to claim 2, wherein the photoresist technique used is [an] a standard integrated circuit photoresist technique.